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#### P-CHANNEL ENHANCEMENT MODE MOSFET

## **Product Summary**

BV <sub>DSS</sub>	R <sub>DS(ON)</sub> max	I <sub>D</sub> T <sub>A</sub> = +25°C
	$45 \text{m}\Omega$ @ $V_{GS} = -4.5V$	-4.3A
-20V	$58m\Omega @ V_{GS} = -2.5V$	-3.8A
	90mΩ @ V <sub>GS</sub> = -1.8V	-3.1A

## **Description**

This new generation MOSFET is designed to minimize the on-state resistance (R<sub>DS(ON)</sub>) and yet maintain superior switching performance, making it ideal for high efficiency power management applications.

## **Applications**

- DC-DC Converters
- Power Management Functions

SOT23





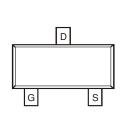
Top View

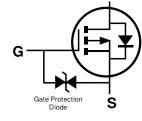
### **Features**

- Low On-Resistance
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- ESD Protected Gate
- Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)

### **Mechanical Data**

- Case: SOT23
- Case Material: Molded Plastic, "Green" Molding Compound.
  UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin Annealed over Copper Leadframe.
  Solderable per MIL-STD-202, Method 208 63
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)





Top View Internal Schematic

**Equivalent Circuit** 

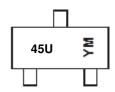
### **Ordering Information** (Note 4)

Part Number	Number Compliance Case		Packaging	
DMP2045U-7	Standard	SOT23	3,000/Tape & Reel	
DMP2045U-13	Standard	SOT23	10,000/Tape & Reel	

Notes:

- 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS), 2011/65/EU (RoHS 2) & 2015/863/EU (RoHS 3) compliant.
- 2. See https://www.diodes.com/quality/lead-free/ for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at https://www.diodes.com/design/support/packaging/diodes-packaging/

## **Marking Information**



45U = Product Type Marking Code YM or $\overline{Y}$ M = Date Code Marking Y or $\overline{Y}$  = Year (ex: F = 2018) M = Month (ex: 9 = September)

Date Code Key

Year	2017	20	18	2019	20	020	2021	2	2022	2023		2024
Code	E	F		G		Н			J	K		L
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D



## 

Characteristic	Symbol	Value	Unit	
Drain-Source Voltage	$V_{DSS}$	-20	V	
Gate-Source Voltage	$V_{GSS}$	±8	V	
Continuous Drain Current (Note 6) $V_{GS} = -4.5V$ Steady $T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$		I <sub>D</sub>	-4.3 -3.5	А
Maximum Continuous Body Diode Forward Current (	Is	-1.2	Α	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)	I <sub>DM</sub>	-25	Α	

## Thermal Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit	
Total Power Dissipation (Note 5)		$P_{D}$	0.8	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	$R_{\theta JA}$	154	°C/W
Total Power Dissipation (Note 6)		P <sub>D</sub>	1.2	W
Thermal Resistance, Junction to Ambient (Note 6)	Steady State	$R_{ heta JA}$	98	°C/W
Operating and Storage Temperature Range		T <sub>J</sub> , T <sub>STG</sub>	-55 to +150	°C

# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 7)						
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	-20	_	_	V	$V_{GS} = 0V, I_D = -250\mu A$
Zero Gate Voltage Drain Current $T_J = +25$ °C	I <sub>DSS</sub>	_	_	-1	μΑ	$V_{DS} = -20V, V_{GS} = 0V$
Gate-Source Leakage	I <sub>GSS</sub>	_	_	±10	μΑ	$V_{GS} = \pm 8.0V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 7)						
Gate Threshold Voltage	V <sub>GS(TH)</sub>	-0.3	_	-1.0	V	$V_{DS} = V_{GS}$ , $I_D = -250\mu A$
		_	32	45		$V_{GS} = -4.5V$ , $I_D = -4.0A$
Static Drain-Source On-Resistance	R <sub>DS(ON)</sub>	_	42	58	mΩ	$V_{GS} = -2.5V, I_D = -3.5A$
		_	54	90		V <sub>GS</sub> = -1.8V, I <sub>D</sub> = -1.0A
Diode Forward Voltage	$V_{SD}$	_	-0.7	-1.2	V	V <sub>GS</sub> = 0V, I <sub>S</sub> = -1.0A
DYNAMIC CHARACTERISTICS (Note 8)	DYNAMIC CHARACTERISTICS (Note 8)					
Input Capacitance	Ciss	_	634	_	pF	.,
Output Capacitance	Coss	_	81	_	pF	$V_{DS} = -10V, V_{GS} = 0V$ f = 1.0MHz
Reverse Transfer Capacitance	C <sub>rss</sub>	_	66	_	pF	1 - 1.0101112
Gate Resistance	$R_g$	_	20	_	Ω	$V_{DS} = 0V$ , $V_{GS} = 0V$ , $f = 1.0MHz$
Total Gate Charge	Qg	_	6.8	_	nC	
Gate-Source Charge	$Q_{gs}$	_	0.7	_	nC	$V_{GS} = -4.5V, V_{DS} = -10V$ $I_{D} = -4A$
Gate-Drain Charge	$Q_{gd}$	_	1.6	_	nC	1D = -4A
Turn-On Delay Time	t <sub>D(ON)</sub>	_	4.2	_	ns	
Turn-On Rise Time	t <sub>R</sub>	_	3.4	_	ns	$V_{DD} = -10V, V_{GS} = -4.5V,$
Turn-Off Delay Time	t <sub>D(OFF)</sub>		23	_	ns	$R_L = 3.3\Omega$ , $R_G = 1\Omega$
Turn-Off Fall Time	t <sub>F</sub>		9.6	_	ns	
Reverse Recovery Time	t <sub>RR</sub>		1.8	_	ns	I <sub>F</sub> = -1.0A, di/dt = 100A/μs
Reverse Recovery Charge	Q <sub>RR</sub>	_	9.4	_	nC	I <sub>F</sub> = -1.0A, di/dt = 100A/μs

Notes: 5. Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.

<sup>6.</sup> Device mounted on FR-4 substrate PC board, 2oz copper, with 1inch square copper plate.

<sup>7.</sup> Short duration pulse test used to minimize self-heating effect.

<sup>8.</sup> Guaranteed by design. Not subject to product testing.





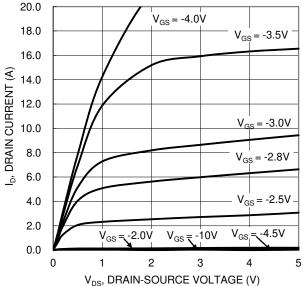


Figure 1. Typical Output Characteristic

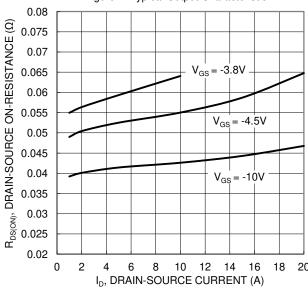


Figure 3. Typical On-Resistance vs. Drain Current and Gate Voltage

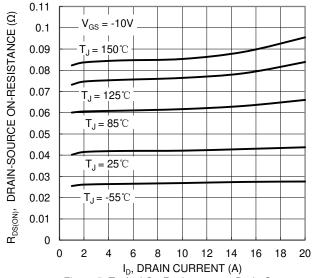


Figure 5. Typical On-Resistance vs. Drain Current and Junction Temperature

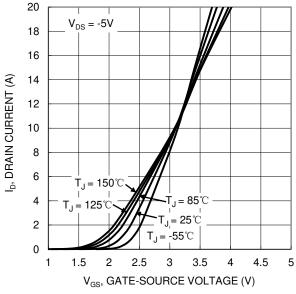


Figure 2. Typical Transfer Characteristic

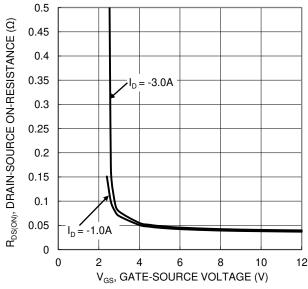


Figure 4. Typical Transfer Characteristic

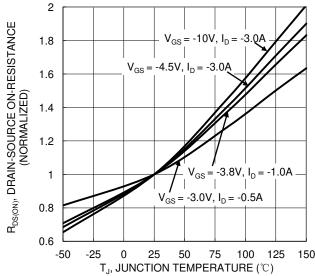
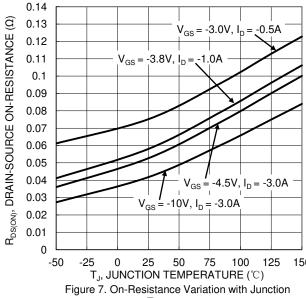
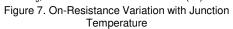


Figure 6. On-Resistance Variation with Junction Temperature









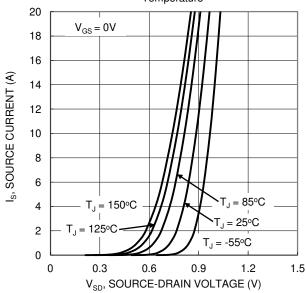
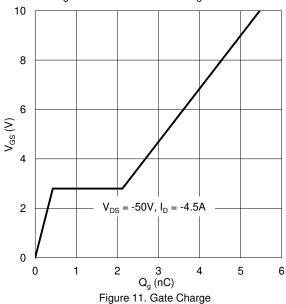


Figure 9. Diode Forward Voltage vs. Current



1.8  $V_{GS(TH)},$  GATE THRESHOLD VOLTAGE (V) 1.5  $I_D = -1mA$ 1.2  $I_D = -250 \mu A$ 0.9 0.6 -50 -25 25 50 75 100 125

 $T_J,$  JUNCTION TEMPERATURE  $({}^{\circlearrowright})$  Figure 8. Gate Threshold Variation vs. Junction Temperature

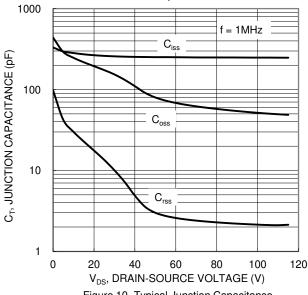
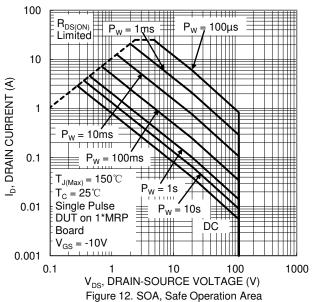


Figure 10. Typical Junction Capacitance





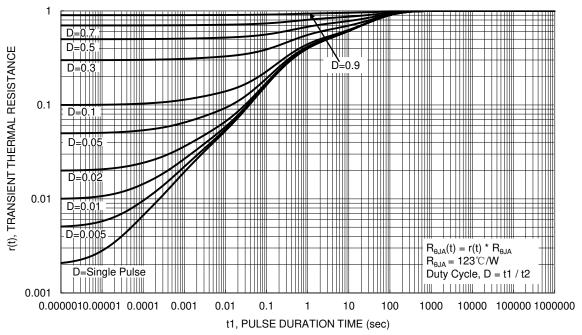


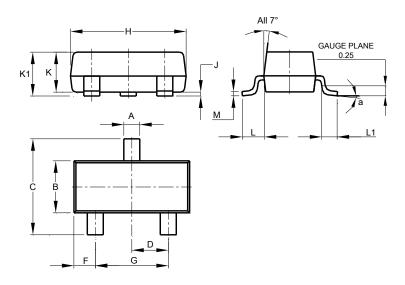
Figure 13. Transient Thermal Resistance



## **Package Outline Dimensions**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23

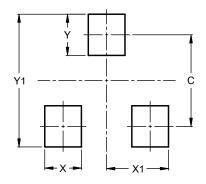


	SOT23						
Dim	Min	Max	Тур				
Α	0.37	0.51	0.40				
В	1.20	1.40	1.30				
С	2.30	2.50	2.40				
D	0.89	1.03	0.915				
F	0.45	0.60	0.535				
G	1.78	2.05	1.83				
Н	2.80	3.00	2.90				
J	0.013	0.10	0.05				
K	0.890	1.00	0.975				
K1	0.903	1.10	1.025				
L	0.45	0.61	0.55				
L1	0.25	0.55	0.40				
M	0.085	0.150	0.110				
а	a 0° 8°						
All Dimensions in mm							

## **Suggested Pad Layout**

Please see http://www.diodes.com/package-outlines.html for the latest version.

### SOT23



Dimensions	Value (in mm)
С	2.0
Х	0.8
X1	1.35
Υ	0.9
Y1	2.9



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